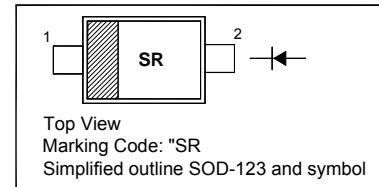


1N5819W

1 A Surface Mount Schottky Barrier Diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	40	V
Average Forward Rectified Current	$I_{F(AV)}$	1	A
Non-Repetitive Peak Forward Surge Current (8.3 ms Single Half Sine-Wave)	I_{FSM}	9	A
Power Dissipation	P_{tot}	450	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	222	$^\circ\text{C/W}$
Operating Temperature Range	T_j	- 55 to + 125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

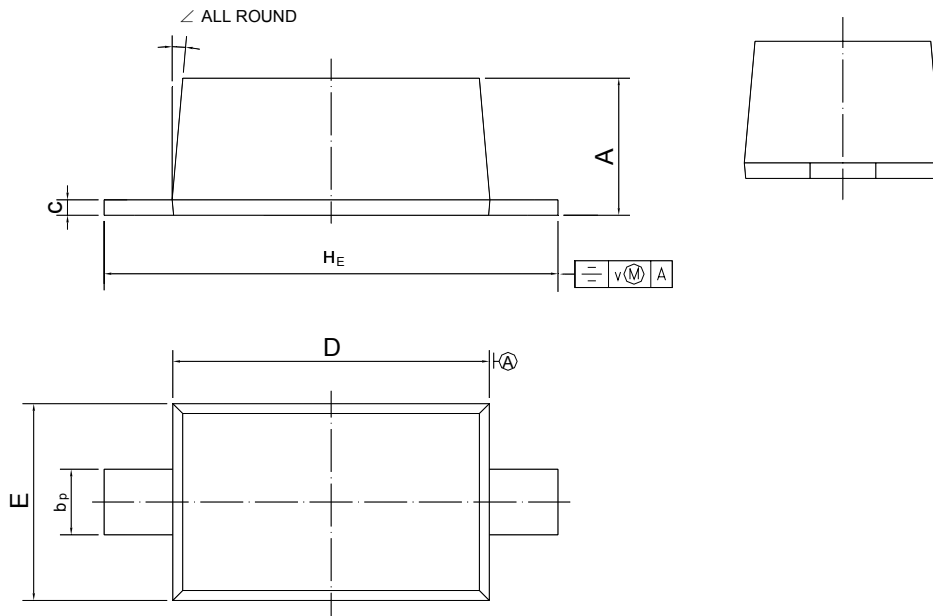
Parameter	Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 1\text{ mA}$	$V_{(BR)R}$	40	-	-	V
Forward Voltage at $I_F = 0.1\text{ A}$ at $I_F = 1\text{ A}$ at $I_F = 3\text{ A}$	V_F	- - -	- - -	0.32 0.45 0.75	V
Reverse Current at $V_R = 40\text{ V}$ at $V_R = 4\text{ V}$ at $V_R = 6\text{ V}$ at $V_R = 40\text{ V}$, $T_a = 100\text{ }^\circ\text{C}$ at $V_R = 4\text{ V}$, $T_a = 100\text{ }^\circ\text{C}$ at $V_R = 6\text{ V}$, $T_a = 100\text{ }^\circ\text{C}$	I_R	- - - - - -	- - - - - -	1 50 75 10 2 3	mA μA μA mA mA mA
Total Capacitance at $V_R = 2\text{ V}$, $f = 1\text{ MHz}$	C_{tot}	-	110	-	pF

1N5819W

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123



UNIT	A	b _p	c	D	E	H _E	v	∠
mm	1.15 1.05	0.6 0.5	0.135 0.100	2.7 2.6	1.65 1.55	3.85 3.55	0.2	5°